

## CLAIMS

1. A ceramic heater for a semiconductor producing/examining  
device comprising: a ceramic substrate; and a resistance heating  
5 element formed on the surface of said ceramic substrate,  
wherein irregularities are formed on the side face of said  
resistance heating element.

2. The ceramic heater according to claim 1,  
10 wherein the size of said irregularities on the side face  
is 100  $\mu\text{m}$  or less.

3. The ceramic heater according to claim 1 or 2,  
wherein said resistance heating element is formed to be  
15 drawn as a curve.

4. The ceramic heater according to any of claims 1 to 3,  
wherein said ceramic substrate is a carbide ceramic or  
a nitride ceramic.  
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